

QuickSwitch® Products High-Speed CMOS 10-Bit Low Resistance Bus Switch with Active High and Low Enables

FEATURES/BENEFITS

- Enhanced N channel FET with no inherent diode to $V_{\rm CC}$
- 2.5 Ω bidirectional switches connect inputs to outputs
- · Zero propagation delay, zero ground bounce
- Undershoot clamp diodes on all switch and control pins
- Available in QSOP and SOIC (SO) packages
- · Active Low and High enable controls
- · Bidirectional signal flow

APPLICATIONS

- Hot-swapping and hot-docking applications (Application Note AN-13)
 - Low R_{ON} resistance for PCI and Compact PCI Applications
- Voltage translation (5V to 3.3V; Application Note AN-11)
- · Power conservation
- · Capacitance reduction and isolation
- Applications requiring Low R_{ON} resistance and active high enabling
- · Bus isolation
- · Clock gating

DESCRIPTION

The QS3R862 provides a set of ten high speed CMOS, TTL-compatible bus switches. The very low ON resistance (2.5Ω) of the QS3R862 allows inputs to be connected to outputs without adding propagation delay and without generating additional ground bounce noise. The switches are controlled by active Low enable ($\overline{\rm BE}$) and active High enable (BE) controls.

The QS3R862 with 2.5Ω R_{ON} resistance is ideal for switching digital buses as well as for hot-plugging, hot-swapping, and hot-docking applications. The low R_{ON} resistance of QS3R862 makes it ideal for PCI, Compact PCI, and VME hot-plugging applications.

Figure 1. Functional Block Diagram

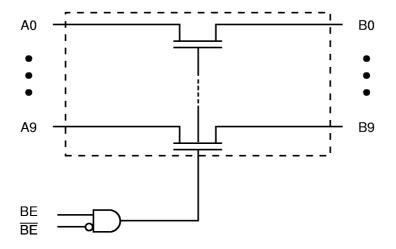


Table 1. Pin Description

Name	I/O	Function
BE	ı	Active Low Bus Enable
BE	ı	Active High Bus Enable
A0-A9	I/O	Bus A
B0-B9	I/O	Bus B

Table 2. Function Table

BE	BE	A0-A9	Function		
L	L	Hi-Z	Disconnect		
L	Н	Hi-Z	Disconnect		
Η	L	B0-B9	Connect		
Н	Н	Hi-Z	Disconnect		

Figure 2. Pin Configuration

(All Pins Top View)

QSOP, SOIC (SO)

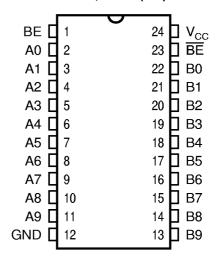


Table 3. Absolute Maximum Ratings

Supply Voltage to Ground	–0.5V to 7.0V
DC Switch Voltage V _S	–0.5V to 7.0V
DC Input Voltage V _{IN}	–0.5V to 7.0V
AC Input Voltage (for a pulse width ≤ 20ns)	–3.0V
DC Output Current Max. Sink Current/Pin	120mA
Maximum Power Dissipation	0.5 watts
T _{STG} Storage Temperature	–65° to 150°C
TSIG Oldrage Temperature	00 10 100 0

Note: ABSOLUTE MAXIMUM CONTINUOUS RATINGS are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum conditions is not implied.

Table 4. Capacitance

 $T_A = 25^{\circ}C, f = 1MHz, V_{IN} = 0V$

	QSOP, SOIC		
Pins	Тур	Max	Unit
Control Inputs	3	4	pF
QuickSwitch Channels (Switch OFF)	5	6	pF

Note: Capacitance is characterized but not production tested. For total capacitance while the switch is ON, please see Section 1 under "Input and Switch Capacitance."

Table 5. DC Electrical Characteristics Over Operating Range

 $T_A = -40$ °C to 85°C, $V_{CC} = 5.0V \pm 10\%$

Symbol	Parameter	Test Conditions	Min	Typ ⁽¹⁾	Max	Unit
V _{IH}	Input HIGH Voltage	Guaranteed Logic HIGH for Control Inputs	2.0			٧
V_{IL}	Input LOW Voltage	Guaranteed Logic LOW for Control Inputs	_	_	0.8	>
I _{IN}	Input Leakage Current (Control Inputs)	$0 \le V_{IN} \le V_{CC}$	_	0.01	1	μΑ
I _{oz}	Off-State Current (Hi-Z)	$0 \le V_{OUT} \le V_{CC}$, Switches Off	_	0.01	1	μΑ
R _{on}	Switch ON Resistance ⁽²⁾	$V_{CC} = Min., V_{IN} = 0.0V,$ $I_{ON} = 30mA$	_	2.5	4	Ω
R _{ON}	Switch ON Resistance ⁽²⁾	$V_{CC} = Min., V_{IN} = 2.4V,$ $I_{ON} = 15mA$	_	4	5.5	Ω
V_{P}	Pass Voltage(3)	$V_{IN} = V_{CC} = 5V$, $I_{OUT} = -5\mu A$	3.7	4	4.3	٧

Notes:

- 1. Typical values indicate V_{CC} = 5.0V and T_A = 25°C. 2. For a diagram explaining the procedure for R_{ON} measurement, please see Section 1 under "DC Electrical Characteristics." Max. value of R_{ON} guaranteed, but not production tested.
- 3. Pass Voltage is guaranteed but not production tested.

Figure 3. Typical ON Resistance vs V_{IN} at $V_{CC} = 5.0V$

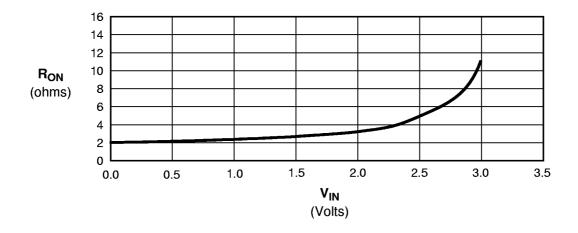


Table 6. Power Supply Characteristics Over Operating Range

 $T_A = -40$ °C to 85°C, $V_{CC} = 5.0V \pm 10$ %

Symbol	Parameter	Test Conditions(1)	Typ(2)	Max	Unit
I _{CCQ}	Quiescent Power Supply Current	$V_{CC} = Max., V_{IN} = GND \text{ or } V_{CC}, f = 0$	0.2	3.0	μА
ΔI_{CC}	Power Supply Current per Input HIGH	$V_{CC} = Max., V_{IN} = 3.4V^{(3)}, f = 0$ per Control Input	_	2.5	mA
Q _{CCD}	Dynamic Power Supply Current per MHz ⁽⁴⁾	V _{CC} = Max., A and B Pins Open, BE or BE Inputs Toggling @ 50% Duty Cycle	_	0.25	mA/ MHz

Notes:

- 1. For conditions shown as Min. or Max., use the appropriate values specified under DC specifications.
- 2. Typical Values are at $V_{CC} = 5.0V$, 25°C Ambient.
- 3. Per TTL driven input ($V_{IN} = 3.4V$, control inputs only). A and B pins do not contribute to ΔI_{CC} .
- 4. This current applies to the control inputs only and represents the current required to switch internal capacitance at the specified frequency. The A and B inputs generate no significant AC or DC currents as they transition. This parameter is guaranteed, but not production tested.

Table 7. Switching Characteristics Over Operating Range

 $T_A = -40$ °C to 85°C, $V_{CC} = 5.0V \pm 10$ %

 C_{LOAD} = 50pF, R_{LOAD} = 500 Ω unless otherwise noted.

Symbol	Description ⁽¹⁾	Min	Тур	Max	Unit
t _{PLH} t _{PHL}	Data Propagation Delay ^(2,4) A to B or B to A	_	_	0.12(3)	ns
t _{PZL} t _{PZH}	Switch Turn-on Delay BE or BE to A or B	1.5	_	5.6	ns
t _{PLZ} t _{PHZ}	Switch Turn-off Delay ⁽²⁾ BE or BE to A or B	1.5	_	4.5	ns

Notes:

- 1. See Test Circuit and Waveforms. Minimums guaranteed but not production tested.
- 2. This parameter is guaranteed, but not production tested.
- 3. The time constant for the switch alone is of the order of 0.12ns for QS3R862 at C_L = 50pF. The bus switch contributes no propagation delay other than the RC delay of the ON resistance of the switch and the load capacitance. Since this time constant is much smaller than the rise/fall times of typical driving signals, it adds very little propagation delay to the system. Propagation delay of the bus switch when used in a system is determined by the driving circuit on the driving side of the switch and its interaction with the load on the driven side.